MSC050SDA070B

Datasheet

Zero Recovery Silicon Carbide Schottky Diode

Final

May 2018

Microsemi

Power Matters.

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1 Revision History

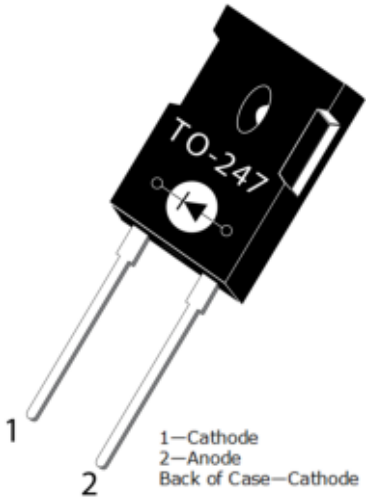
The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision A

Revision A was published in May 2018. It is the first publication of this document.

2 Product Overview

This section shows the product overview for the MSC050SDA070B device.



2.1 Features

The following are key features of the MSC050SDA070B device:

- Ultra-fast recovery times
- Soft recovery characteristics
- Low forward voltage
- Low leakage current
- Avalanche energy rated
- RoHS compliant

2.2 Benefits

The following are benefits of the MSC050SDA070B device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

2.3 Applications

The MSC050SDA070B device is designed for the following applications:

- Power Factor Correction (PFC)
- Anti-parallel diode
  - Switch-mode power supply
  - Inverters/converters
  - Motor controllers
- Freewheeling diode
  - Switch-mode power supply
  - Inverters/converters
- Snubber/clamp diode

3 Electrical Specifications

This section shows the electrical specifications for the MSC050SDA070B device.

3.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC050SDA070B device.

All ratings: T_C = 25 °C unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_R	Maximum DC reverse voltage	700	V
V_{RRM}	Maximum peak repetitive reverse voltage	700	
V_{RWM}	Maximum working peak reverse voltage	700	
I_F	Maximum DC forward current (T_c = 25 °C)	88	A
	Maximum DC forward current (T_c = 135 °C)	39	
	Maximum DC forward current (T_c = 145 °C)	32	
I_{FRM}	Repetitive peak forward surge current (T_c = 25 °C, t_p = 10 ms, half sine wave)	128	
I_{FSM}	Non-repetitive forward surge current (T_c = 25 °C, t_p = 10 ms, half sine wave)	124	
P_{tot}	Power dissipation (T_c = 25 °C)	283	W
	Power dissipation (T_c = 110 °C)	123	
T_J , T_{STG}	Operating and storage temperature range	–55 to 175	°C
T_L	Lead temperature for 10 seconds	300	
E_{AS}	Single-pulse avalanche energy (starting T_J = 25 °C, L = 0.08 mH, peak I_L = 50 A)	100	mJ

The following table shows the thermal and mechanical characteristics of the MSC050SDA70B device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0.37	0.53	°C/W
W_T	Package weight		0.22		oz
			5.9		g
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m

3.2 Electrical Performance

The following table shows the static characteristics of the MSC050SDA070B device.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Typ	Max	Unit
V_F	Forward voltage	I_F = 50 A, T_J = 25 °C	1.5	1.8	V
		I_F = 50 A, T_J = 175 °C	1.9		
I_{RM}	Reverse leakage current	V_R = 700 V, T_J = 25 °C	15	200	µA
		V_R = 700 V, T_J = 175 °C	250		
Q_C	Total capacitive charge	V_R = 400 V, T_J = 25 °C	133		nC
C_J	Junction capacitance	V_R = 1 V, T_J = 25 °C, ƒ = 1 MHz	2034		pF
	Junction capacitance	V_R = 200 V, T_J = 25 °C, ƒ = 1 MHz	248		
	Junction capacitance	V_R = 400 V, T_J = 25 °C, ƒ = 1 MHz	216		

3.3 Performance Curves

This section shows the typical performance curves for the MSC050SDA070B device.

Figure 1 • Maximum Transient Thermal Impedance

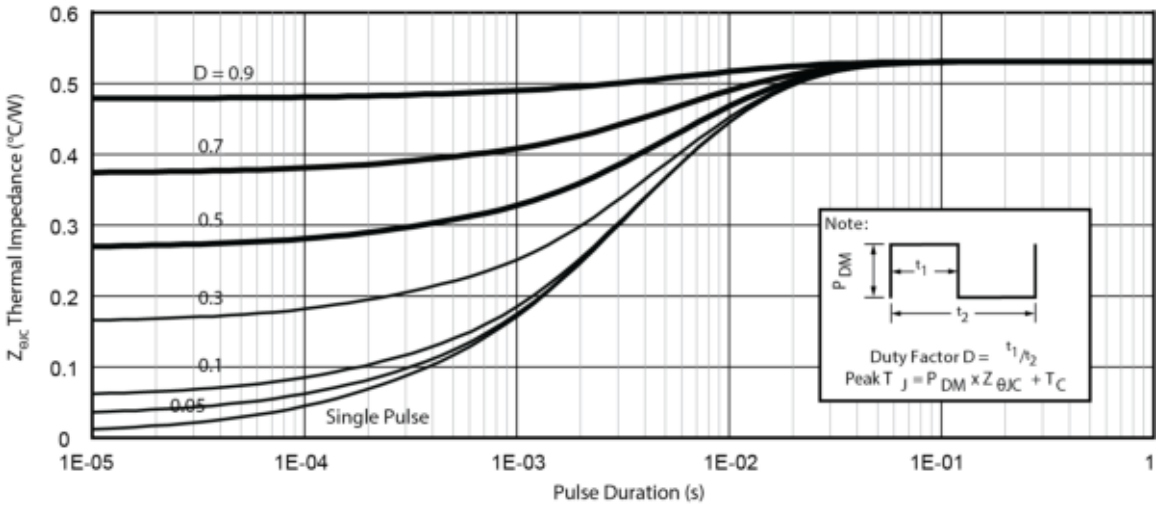


Figure 2 • Forward Current vs Forward Voltage

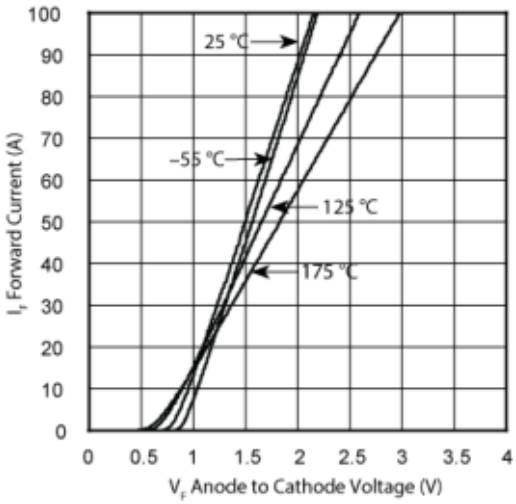


Figure 3 • Max Forward Current vs Case Temp

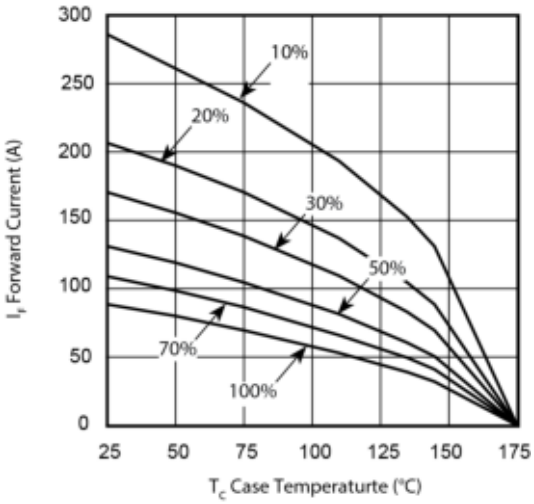


Figure 4 • Max Power Dissipation vs Case Temp

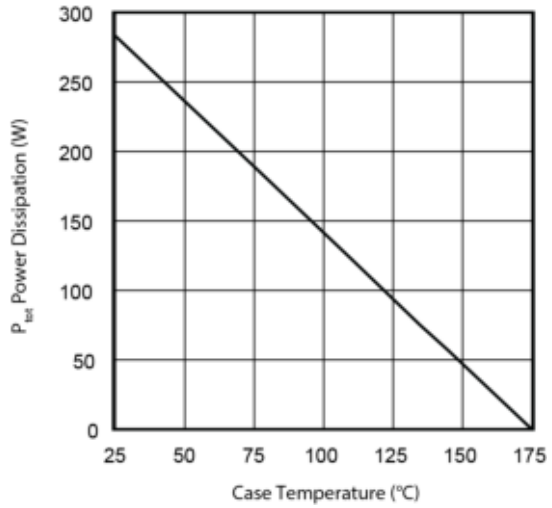


Figure 5 • Reverse Current vs. Reverse Voltage

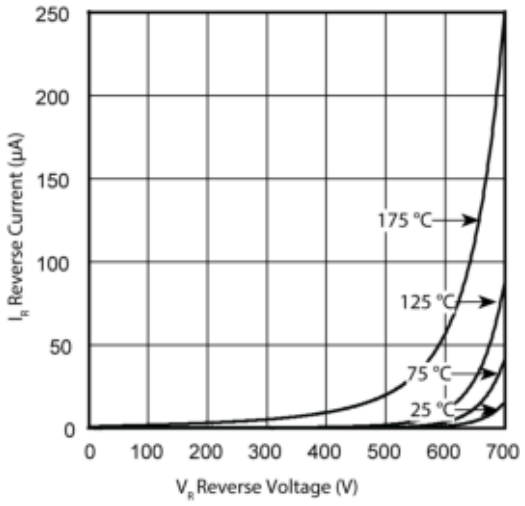


Figure 6 • Total Capacitive Charge vs. Reverse Voltage

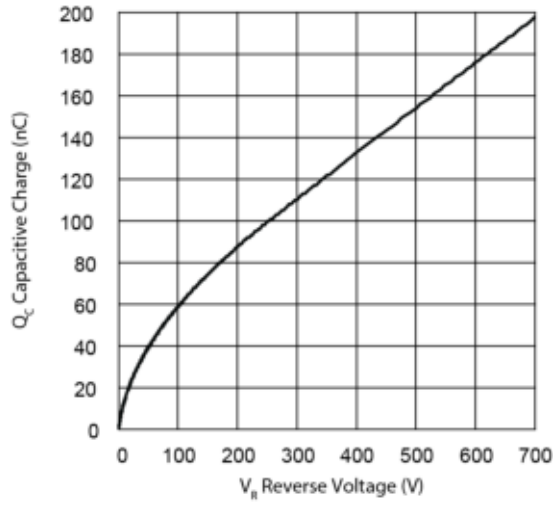
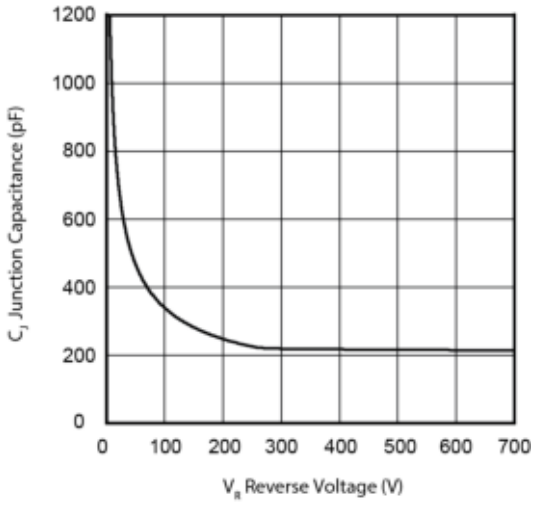


Figure 7 • Junction Capacitance vs Reverse Voltage



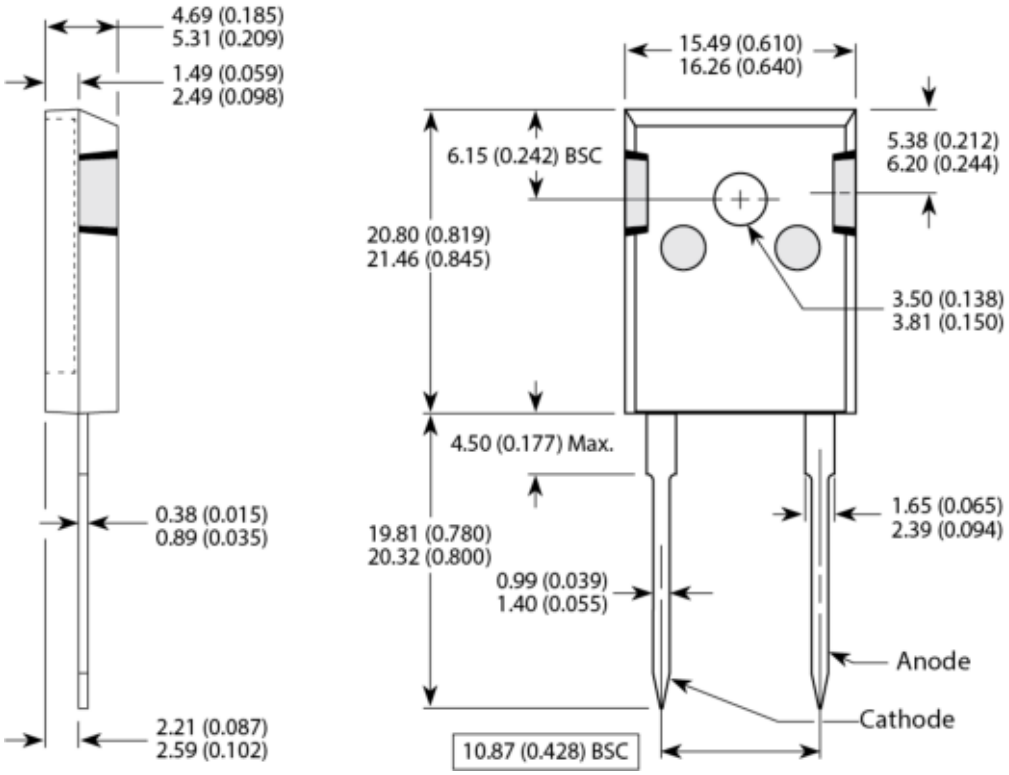
4 Package Specification

This section outlines the package specification for the MSC050SDA070B device.

4.1 Package Outline Drawing

This section shows the TO-247 package drawing of the MSC050SDA070B device. Dimensions are in millimeters and (inches).

Figure 8 • Package Outline Drawing



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